SESSION XII

Reliability II

Chair: Walter Bloss, Aerospace Corp.

This session addresses the important reliability issues of power slump and effective reliability testing in GaAs devices. The first paper describes a method to screen MESFETs for power slump using accelerated DC stress testing. A number of MESFETs from different companies were measured and figures of merit against power slump were determined. The second paper develops a method that uses step stressing to project device lifetime and activation energies. This method has been extended to analyze voltage accelerated power drift in HEMTs.